

# SDA-7000

GaAs Distributed Amplifier

RFMD's SDA-7000 is a directly coupled (DC) GaAs microwave monolithic integrated circuit (MMIC) distributed driver amplifier die designed to support a wide array of high frequency commercial, military, and space applications. They are ideal for wideband amplifier gain blocks, modulators, clock drivers, broadband automated test equipment (ATE), military, and aerospace applications.



Functional Block Diagram



Package: Die, 2.40mm x 1.21mm x 0.102mm

## **Features**

- DC to 40GHz Operation
- Gain = 11dB Typical
- Noise Figure = 5dB Typical
- 200mA Total Current

## **Applications**

- Drive for Single-Ended (SE) MZM
- NRZ, DPSK, ODB, RZ
- Clock Driver for RZ and CS Pulse Carver
- Broadband ATE
- Instrumentation
- Military
- Aerospace

# **Ordering Information**

SDA-7000GaAs Distributed Amplifier, GelPak, 10 pieces or moreSDA-7000SBSample Bag, GaAs Distributed Amplifier, GelPak, 2 pieces



## **Absolute Maximum Ratings**

Parameter	Rating	Unit
Drain Bias Voltage (V <sub>DD</sub> )	+9.0	V <sub>DC</sub>
Gate Bias Voltage (V <sub>TI</sub> )	-2 to +1	V <sub>DC</sub>
Gate Bias Voltage (V <sub>G2</sub> )	(V <sub>DD</sub> -5.0) to V <sub>DD</sub>	V <sub>DC</sub>
RF Input Power ( $V_{DD}$ = +7.0 $V_{DC}$ )	+15	dBm
Operating Junction Temperature (T <sub>J</sub> )	+175	°C
Continuous Power Dissipation (T = +85°C)	1400	mW
Thermal Resistance (Pad to Die Bottom)	63	°C/W
Storage Temperature	-40 to +150	°C
Operating Temperature	-40 to +85	°C
ESD JESD22-A114 Human Body Model (HBM)	Class 0 (All Pads)	





RFMD Green: RoHS compliant per EU Directive 2011/65/EU, halogen free per IEC 61249-2-21, <1000ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony solder.

Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

### **Nominal Operating Parameters**

Deremeter	Specification			11		
Parameter	Min	Тур	Мах	Unit	Condition	
General Performance					$T_A = +25^{\circ}C, V_{DD} = +7V, V_{G2} = +3.2V_{DC},$ $I_{DD} = 200mA^*$	
Operating Frequency	DC		40	GHz	3dB BW	
Gain		11		dB		
Output Voltage		8		$V_{P-P}$		
OIP3 at Mid-Band		32		dBm		
P1dB at Mid-Band		21		dBm	20GHz	
P3dB at Mid-Band		23		dBm	20GHz	
Noise Figure at Mid-Band		5.0		dB	20GHz	
Input Return Loss		12		dB	DC to 40GHz	
Output Return Loss		12		dB	DC to 40GHz	
Supply Current		200		mA		
Supply Voltage		5,7		$V_{\text{DC}}$		

\*Adjust VTI between -2.0V<sub>DC</sub> to +1.0V<sub>DC</sub> to achieve  $I_{DD}$  = 200mA typical. NOTE: The SDA-7000 can also be operated at  $V_{DD}$  =  $5V_{DC}$ ,  $V_{G2}$  = 2.2V<sub>DC</sub>

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# Typical Performance: $V_{DD} = 5.0V$ , $V_{G2} = 2.2V$

(See section at the end of the data sheet for measurement comments)



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# Typical Performance: $V_{DD} = 5.0V$ , $V_{G2} = 2.2V$ (Continued)



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5

0

0

5

10

15





# Typical Performance: $V_{DD} = 7.0V$ , $V_{G2} = 3.2V$

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20

Fre que ncy (GHz)

25

30

35

40

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5

0

0

5

10

15

20

Frequency (GHz)

25

30

35

40

-40C

25C

85C

-40C

25 C

85 C

250

-40C

85C

40

40



# Typical Performance: V<sub>DD</sub> = 7.0V, V<sub>G2</sub> = 3.2V (Continued)



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# **Application Schematic**



## Die Drawing (Dimensions in microns)



Notes:

- 1. No connection required for unlabeled bond pads
- 2. Die thickness is 0.102mm (4mil)
- 3. Typical bond pad is 0.100mm square
- 4. Backside metallization: gold
- 5. Backside metal is ground
- 6. Bond pad metallization: gold

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## **Pin Names and Descriptions**

Pin	Name	Description	Interface Schematic
1	RFIN	RF Input. This pad is DC coupled and matched to $50\Omega$ from DC to 40GHz. $50\Omega$ microstrip transmission line on 0.127mm (5mil) thick alumina thin film substrate is recommended for RF input and output. A DC blocking capacitor is required for this connection. The calue of this capacitor will be based on the desired frequency range of application.	
2	VG2	Each amplifier stage in the SDA-7000 is a cascade configuration. The gate of each upper FET in the cascade amplifiers is biased with the $2.2V_{DC}$ (for $V_{DD}$ = 5V) or $3.2V_{DC}$ (for $V_{DD}$ = 7V) supply mentioned in this data sheet. The DC connection for the upper device gates runs across the length of the die. Pads 2 and 5 are both on this DC connection but are on opposite ends of the die. The $V_{DC}$ connection can therefore be placed on either pad. A bypass capacitor is recommended on both ends, pads 2 and 5.	1000 pF
3	νто	The output drain termination pad. This pad requires a 1000pF bypass capacitor with the shortest wirebond length to prevent low frequency gain ripple.	1000 pF
4	RFOUT and VDD	RF Output. 50 $\Omega$ microstrip transmission line on 0.127mm (5mil) thick alumina thin film substrate is recommended for RF input and output. Connect the DC bias (V <sub>DD</sub> ) network to provide drain current (I <sub>DD</sub> ). Note: Drain Bias (V <sub>DD</sub> ) must be applied through a broadband bias tee or external bias network.	1000 pF VDD VDD VDD VDD VDD VDD RFOUT Note: Drain Bias (VDD) must be applied through a broadband bias tee or external bias network
5	VCAS	Each amplifier stage in the SDA-7000 is a cascade configuration. The gate of each upper FET in the cascade amplifiers is biased with the $2.2V_{DC}$ (for $V_{DD} = 5V$ ) or $3.2V_{DC}$ (for $V_{DD} = 7V$ ) supply mentioned in this data sheet. The DC connection for the upper device gates runs across the length of the die. Pads 2 and 5 are both on this DC connection but are on opposite ends of the die. The $V_{G2}$ connection can therefore be placed on either pad. A bypass capacitor is recommended on both ends, pads 2 and 5.	1000 pF
6	VG21	Not connected.	
7	VTI	Input gate voltage for the lower devices in the cascade amplifier. This pad also serves as the RF ground for the input termination resistor. The DC voltage applied to this pad will be between $-2.0V_{DC}$ (device is pinched OFF) to $+1.0V_{DC}$ (fully ON). The value of this capacitor will effect the low frequency response of the amplifier.	1000 pF
Die	GND	Ground connection. Connect die bottom directly to ground plane for best performance. NOTE: The die should be connected directly to the ground plane with conductive epoxy.	

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## **Bias Sequence (Turn Device On):**

- VTI Apply negative -2.0 volts. (This shuts the device off.)
- VG2 Apply positive 2.2 volts.
- VDD Apply positive 7.0 volts to the RF output bias tee.

Important - Adjust VTI between -2 to +1.0 volts to achieve IDD = 200mA nominal.

### **Bias Sequence (Turn Device Off):**

- VTI Return to negative -2.0 volts.
- VDD Remove positive 7.0 volts to the RF output bias tee.
- VG2 Remove positive 2.2 volts.

### **Assembly Diagram**



#### **Measurement Technique**

All data presented in this document represents the integrated circuit and accompanying bond wires.

All performance data reported in this document were measured in the following manner. Data was taken using a temperature controlled probe station utilizing 150  $\mu$ m pitch GSG probes. The interface between the probes and integrated circuit was made with a coplanar to microstrip ceramic test interface. The test interface was wire bonded to the die using 1 mil diameter bondwires. The spacing between the test interface and the die was 200  $\mu$ m, and the bond wire loop height was 100  $\mu$ m. The calibration of the test fixture included the probes and test interfaces, so that the measurement reference plane was at the point of bond wire attachment to the ceramic interface. The presented data therefore represents the chip plus wirebonds.